

Title (en)  
PROCESS FOR PRODUCING POLYCRYSTALLINE SILICON

Title (de)  
VERFAHREN ZUR HERSTELLUNG VON POLYKRISTALLINEM SILICIUM

Title (fr)  
PROCÉDÉ DE PRODUCTION DE SILICIUM POLYCRISTALLIN

Publication  
**EP 3071484 A1 20160928 (DE)**

Application  
**EP 14805502 A 20141105**

Priority  
• DE 102013223883 A 20131122  
• EP 2014073798 W 20141105

Abstract (en)  
[origin: WO2015074872A1] The invention relates to a process for producing polycrystalline silicon comprising provision of polycrystalline silicon rods, comminution of the polycrystalline silicon rods to give polycrystalline silicon fragments and packing of the polycrystalline silicon fragments by introduction of the polycrystalline silicon fragments into a strong and intrinsically stable container having a base, a wall and an aperture, where the container has the shape of a truncated cone or truncated pyramid with two differently sized areas of base and aperture and with a lateral area, where the area of the base is greater than the area of the aperture of the container, where the thickness of the wall of the container is at least 0.5 mm and where an angle between a slant-height line and a vertical axis of cone or pyramid is at least 2°.

IPC 8 full level  
**B65B 25/00** (2006.01); **B65B 5/06** (2006.01); **B65B 29/00** (2006.01); **B65D 1/18** (2006.01); **B65D 30/28** (2006.01); **C01B 33/02** (2006.01)

CPC (source: CN EP KR US)  
**B02C 23/08** (2013.01 - US); **B65B 5/06** (2013.01 - EP KR US); **B65B 25/00** (2013.01 - EP KR US); **B65B 29/00** (2013.01 - EP KR US); **B65B 67/02** (2013.01 - EP KR US); **B65D 1/18** (2013.01 - EP KR US); **B65D 11/10** (2013.01 - CN); **B65D 25/101** (2013.01 - CN); **C01B 33/02** (2013.01 - EP US); **C01B 33/035** (2013.01 - EP KR US)

Citation (search report)  
See references of WO 2015074872A1

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**WO 2015074872 A1 20150528**; **WO 2015074872 A9 20150723**; CA 2927710 A1 20150528; CA 2927710 C 20180116; CN 105764801 A 20160713; DE 102013223883 A1 20150528; EP 3071484 A1 20160928; JP 2016539069 A 20161215; JP 6203959 B2 20170927; KR 20160088927 A 20160726; TW 201520137 A 20150601; TW I547419 B 20160901; US 2016264276 A1 20160915

DOCDB simple family (application)  
**EP 2014073798 W 20141105**; CA 2927710 A 20141105; CN 201480063994 A 20141105; DE 102013223883 A 20131122; EP 14805502 A 20141105; JP 2016533170 A 20141105; KR 20167016481 A 20141105; TW 103139856 A 20141118; US 201415036888 A 20141105